Amendments to the Claims:

This listing of the claims will replace all prior versions and listings of claims in this application.

Listing of Claims:

What is claimed is:

Claim 1 (Currently Amended). A method of stripping an integrated circuit (IC) structure having a photoresist material, ~~and~~ an organosilicate glass (OSG) material and a via etched into said IC structure, comprising:

feeding a nitrous oxide (N_2O) gas into a reactor;

generating a plasma ~~is~~ in said reactor; stripping said photoresist;

generating an organic plug that occupies said via, and stripping said organic plug with said N_2O gas; and

generating a high selectivity between said photoresist and said OSG.

Claim 2 (Original). The method of claim 1 wherein said photoresist is an organic photoresist.

Claim 3 (Original). The method of claim 2 wherein said stripping said photoresist is one of a plurality of steps performed during a dual damascene process.

Claim 4 (Original). The method of claim 3 wherein said stripping of said photoresist is performed in the same reactor used for etching said OSG material.

Claim 5 (Canceled). ~~The method of clam 1 further comprising, providing a via etched into said IC structure; generating an organic plug that occupies said via; and stripping said organic plug with said N_2O gas.~~

Claim 6 (Currently Amended). A method of stripping an integrated circuit (IC) structure including a first photoresist layer, a second intermediate layer, and a third organosilicate glass (OSG) layer, comprising:

feeding a nitrous oxide (N_2O) gas into a reactor;

generating a plasma in said reactor;

stripping said photoresist with said plasma;

generating a high selectivity between said first photoresist layer and said second intermediate layer;

<u>stripping said second intermediate layer with said plasma;</u> and

generating a high selectivity between said first photoresist layer and said third OSG layer.

Claim 7 (Original). The method of claim 6 wherein said photoresist is an organic photoresist.

Claim 8 (Original). The method of claim 6 wherein said stripping of said photoresist is performed in the same reactor used for etching said OSG layer.

Claim 9 (Original). The method of claim 6 wherein said stripping said photoresist is one of a plurality of steps performed during a dual damascene process.

Claim 10 (Original). The method of claim 6 wherein said second intermediate layer is a cap layer.

Claim 11 (Original). The method of claim 10 wherein said cap layer is a selected from a group consisting of Silicon Dioxide (SiO_2) and Silicon Oxynitride (SiON).

Claim 12 (Original). The method of claim 6 wherein said second intermediate layer is a hardmask layer.

Claim 13 (Original). The method of claim 12 wherein said hardmask layer is selected from a group consisting of Silicon Nitride (Si_3N_4), Tantalum Nitride (TaN), Titanium Nitride (TiN), and Silicon Carbide (SiC).

Claim 14 (Currently Amended). A method of performing a via first etch with an IC structure including a first photoresist layer, a second cap layer, and a third organosilicate glass (OSG) layer, comprising:

~~firstly,~~ etching a via into said second cap layer and said third OSG layer; ~~and~~

~~secondly,~~ stripping said first photoresist layer with a nitrous oxide (N_2O) gas;

generating an organic plug within said via; and

stripping said organic plug with said N_2O gas.

Claim 15 (Currently Amended). The method of claim 14 wherein said ~~further comprising, thirdly, generating an~~ organic plug within ~~with~~ said via ~~that~~ occupies part of said third OSG layer.

Claim 16 (Currently Amended). The method of claim 15 further comprising, ~~fourthly,~~ etching a trench into said second cap layer and said third OSG layer and applying another first photoresist layer.

Claim 17 (Currently Amended). The method of claim 15 further comprising, ~~fifthly,~~ stripping said other first photoresist layer and said organic plug with said N_2O gas.

Claim 18 (Original). The method of claim 17 wherein said photoresist is an organic photoresist.

Claim 19 (Original). The method of 18 wherein said stripping said photoresist is one of a plurality of steps performed during a dual damascene process.

Claim 20 (Currently Amended). A method of performing a trench first etch with an IC structure including a first photoresist layer, a second hardmask layer, and a third organosilicate glass (OSG) layer, comprising:

~~firstly,~~ etching a trench into said second hardmask layer; ~~and~~

~~secondly,~~ stripping said first photoresist layer with a nitrous oxide (N_2O) gas;

applying another first photoresist layer for performing a via etch;

etching a via into said second hardmask layer, and said third OSG layer;

stripping said other first photoresist layer with said N_2O gas;

generating an organic plug within said via, and

using said N_2O gas to strip said organic plug.

Claim 21 (Canceled). ~~The method of claim 20 further comprising, thirdly, applying another first photoresist layer for performing a via etch.~~

Claim 22 (Canceled). ~~The method of claim 21 further comprising, fourthly, etching a via into said second hardmask layer, and said third OSG layer.~~

Claim 23 (Canceled). ~~The method of claim 22 further comprising, fifthly, stripping said other first photoresist layer with said N_2O gas.~~

Claim 24 (Currently Amended). The method of claim 20 ~~23~~ wherein said ~~further comprising, sixthly, generating an~~ organic plug within said via ~~that~~ occupies part of said third OSG layer.

Claim 25 (Currently Amended). The method of claim 24 further comprising, ~~seventhly,~~ etching a second ~~said~~ trench into said third OSG layer.

Claim 26 (Currently Amended). The method of claim 25 further comprising, ~~eighthly,~~ using said N_2O gas to strip said organic plug.